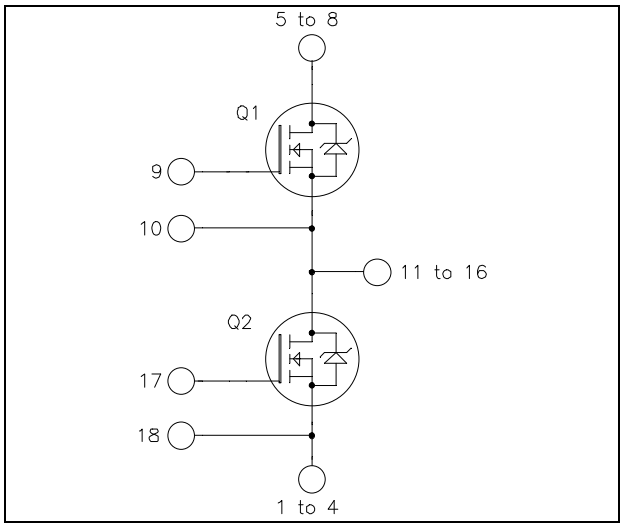
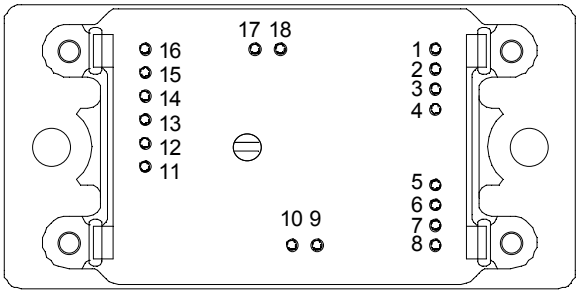
APTC60AM42F2G

Phase leg Super Junction MOSFET Power Module

V_{DSS} = 600V
R_{DSon} = 42mΩ max @ Tj = 25°C
I_D = 66A @ Tc = 25°C





Pins 1/2/3/4 ; 5/6/7/8 ; 11/12/13/14/15/16 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- CoolMOS™
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
  - Fast intrinsic diode
- Very low stray inductance
- Kelvin source for easy drive
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		600	V
I_D	Continuous Drain Current	T_c = 25°C	66	A
		T_c = 80°C	49	
I_{DM}	Pulsed Drain current		200	
V_{GS}	Gate - Source Voltage		±20	V
R_{DSon}	Drain - Source ON Resistance		42	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	416	W
I_{AR}	Avalanche current (repetitive and non repetitive)		20	A
E_{AR}	Repetitive Avalanche Energy		1	mJ
E_{AS}	Single Pulse Avalanche Energy		1800	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V,V_{DS} = 600V			100	µA
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 33A			42	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 6mA	3	4	5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V			±200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz			14.6		nF
C_{oss}	Output Capacitance				3.47		
C_{rss}	Reverse Transfer Capacitance				0.082		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 300V I_D = 66A			510		nC
Q_{gs}	Gate – Source Charge				86		
Q_{gd}	Gate – Drain Charge				270		
$T_{d(on)}$	Turn-on Delay Time	**Inductive Switching @ 125°C** V_{GS} = 15V V_{Bus} = 400V I_D = 66A R_G = 2.5Ω			21		ns
T_r	Rise Time				30		
$T_{d(off)}$	Turn-off Delay Time				240		
T_f	Fall Time				52		
E_{off}	Turn-off Switching Energy	**Inductive switching** V_{GS} = 15V ; I_D = 66A V_{Bus}=400V ; R_G=2.5Ω	T_j = 25°C		1.18		mJ
			T_j = 125°C		1.45		
R_{thJC}	Junction to Case Thermal Resistance					0.3	°C/W

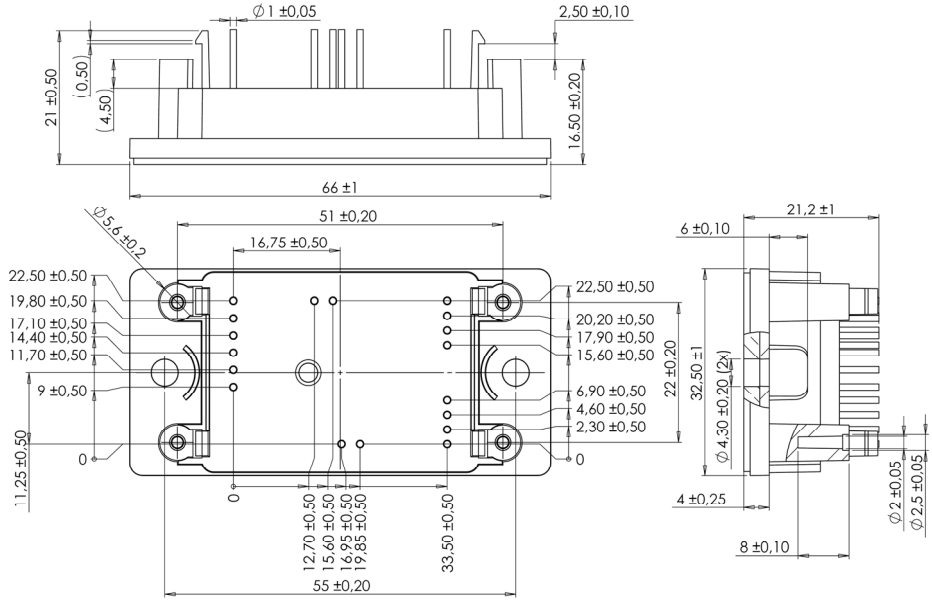
Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)		Tc = 25°C		66		A
			Tc = 80°C		49		
V_{SD}	Diode Forward Voltage	V_{GS} = 0V, I_S = - 66A				1.2	V
dv/dt	Peak Diode Recovery					40	V/ns
t_{rr}	Reverse Recovery Time	I_S = - 66A V_R = 400V di_S/dt = 200A/µs	T_j = 125°C		350		ns
Q_{rr}	Reverse Recovery Charge		T_j =125°C		5.4		µC

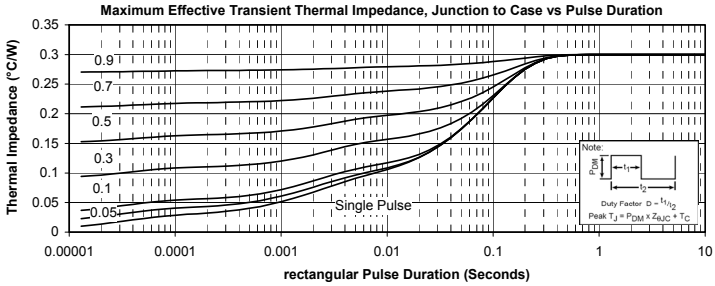
Thermal and package characteristics

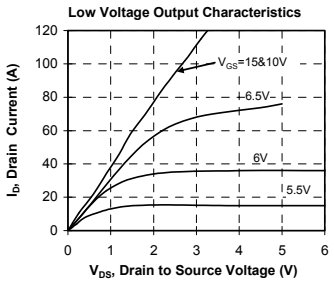
Symbol	Characteristic			Min	Typ	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

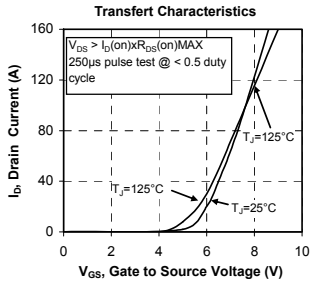
SP2 Package outline (dimensions in mm)

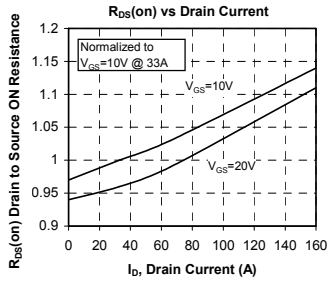


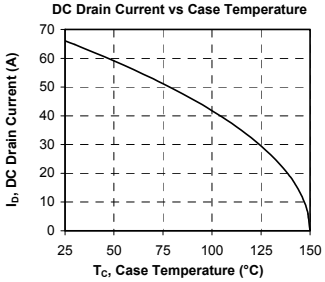
Typical Performance Curve



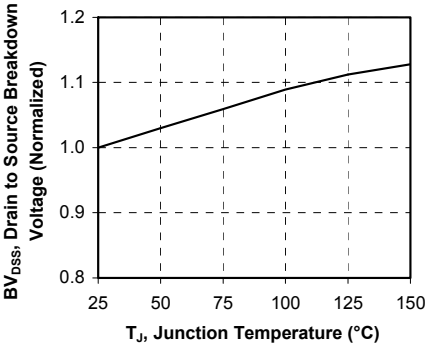




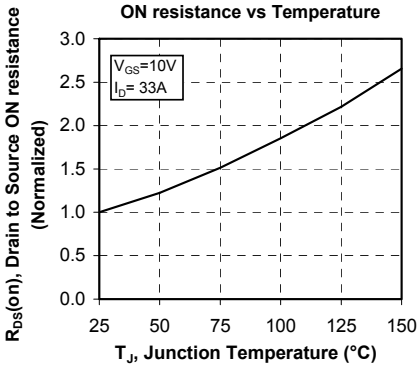




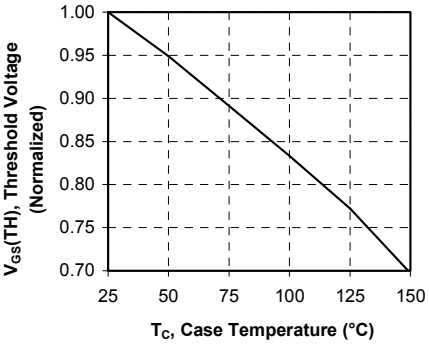
Breakdown Voltage vs Temperature



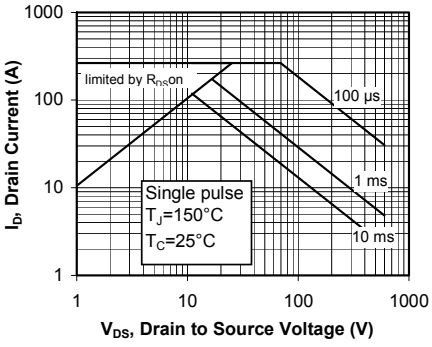
ON resistance vs Temperature



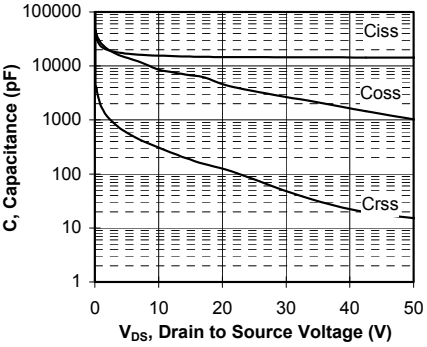
Threshold Voltage vs Temperature



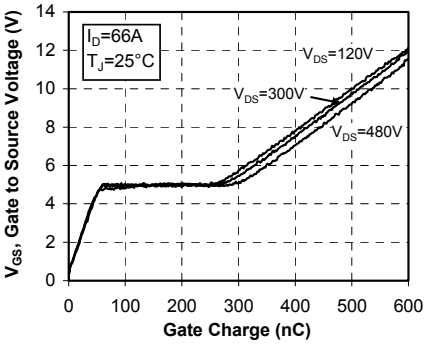
Maximum Safe Operating Area

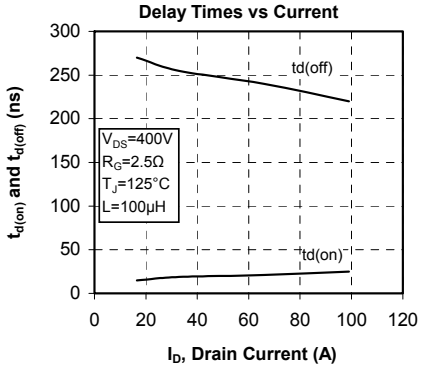


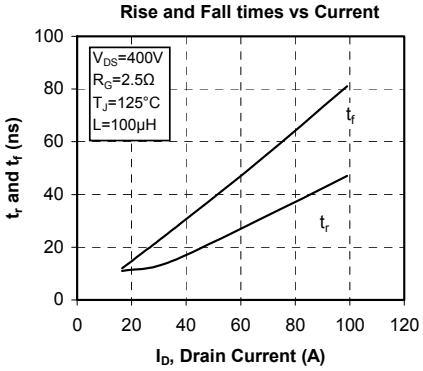
Capacitance vs Drain to Source Voltage

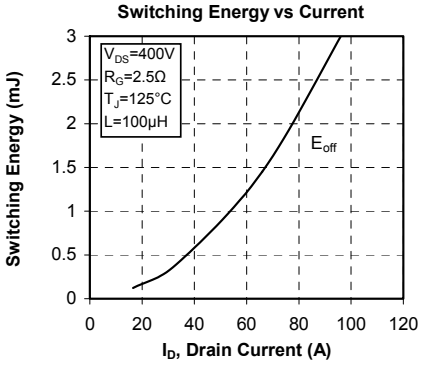


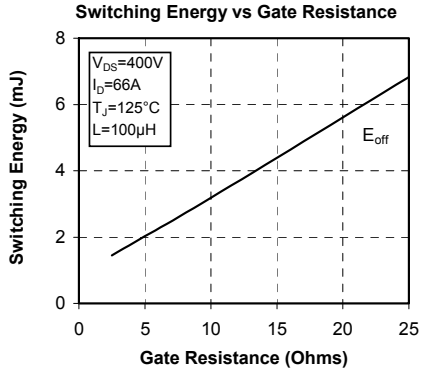
Gate Charge vs Gate to Source Voltage

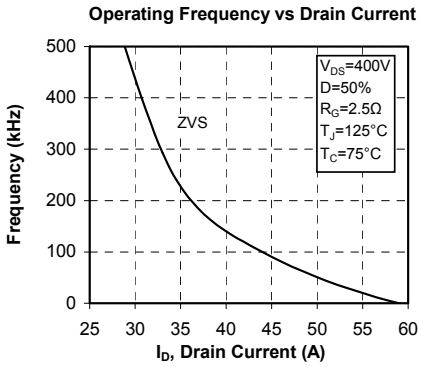


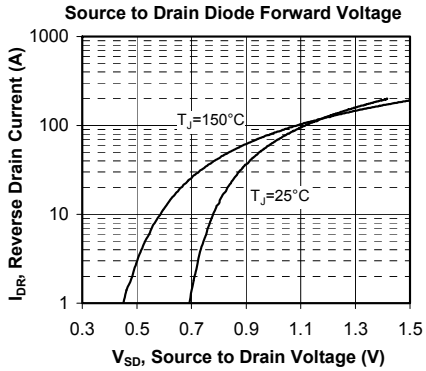












"COOLMOS™ comprise a new family of transistors developed by Infineon Technologies AG. "COOLMOS" is a trademark of Infineon Technologies AG".

DISCLAIMER

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with life-support or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customers final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/legal/tnc.asp

Life Support Application

Seller's Products are not designed, intended, or authorized for use as components in systems intended for space, aviation, surgical implant into the body, in other applications intended to support or sustain life, or for any other application in which the failure of the Seller's Product could create a situation where personal injury, death or property damage or loss may occur (collectively "Life Support Applications").
Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.